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FDN86246

N-Channel PowerTrench® MOSFET

150 V, 1.6 A, 261 mΩ

Features

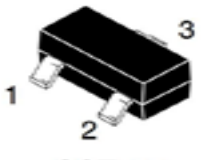
- Max $r_{DS(on)}$ = 261 mΩ at V_{GS} = 10 V, I_D = 1.6 A
- Max $r_{DS(on)}$ = 359 mΩ at V_{GS} = 6 V, I_D = 1.4 A
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

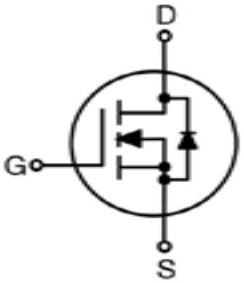
Application

- PD Switch



SOT–23

1 – Gate
2 – Source
3 – Drain



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		150	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	-Continuous	(Note 1a)	1.6	A
	-Pulsed		6	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	13	mJ
P_D	Power Dissipation	(Note 1a)	1.5	W
	Power Dissipation	(Note 1b)	0.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	

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Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		106		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	3.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-9		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 1.6 A		195	261	mΩ
		V_{GS} = 6 V, I_D = 1.4 A		242	359	
		V_{GS} = 10 V, I_D = 1.6 A, T_J = 125 °C		359	481	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 1.6 A		4		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz		168	225	pF
C_{oss}	Output Capacitance			21	30	pF
C_{rss}	Reverse Transfer Capacitance			1.6	5	pF
R_g	Gate Resistance			0.9		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 1.6 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		4.5	10	ns
t_r	Rise Time			1.1	10	ns
$t_{d(off)}$	Turn-Off Delay Time			8	16	ns
t_f	Fall Time			2.9	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 75 V, I_D = 1.6 A		2.9	5	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 5 V; V_{DD} = 75 V, I_D = 1.6 A		1.6	3	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 75 V, I_D = 1.6 A		0.9		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 75 V, I_D = 1.6 A		0.8		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.6 A (Note 2)		0.83	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 1.6 A, di/dt = 100 A/μs		44	70	ns
Q_{rr}	Reverse Recovery Charge	I_F = 1.6 A, di/dt = 100 A/μs		29	47	nC

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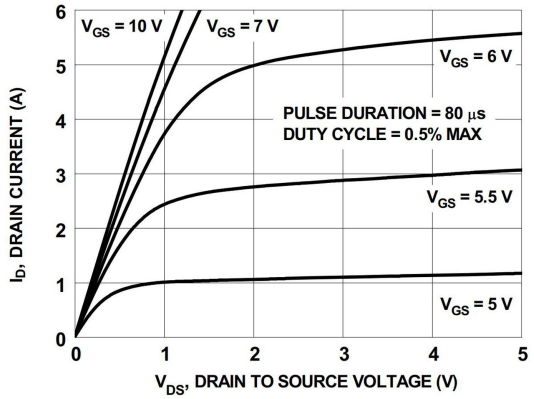


Figure 1. On-Region Characteristics

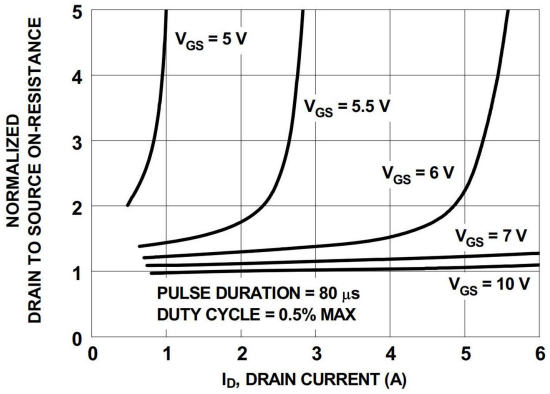


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

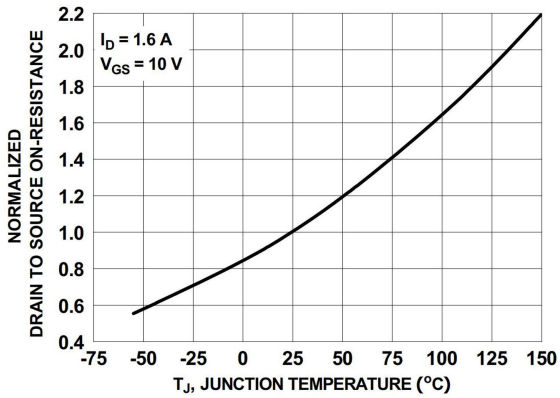


Figure 3. Normalized On-Resistance vs Junction Temperature

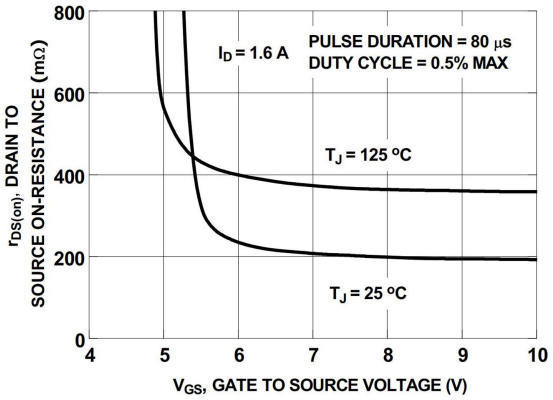


Figure 4. On-Resistance vs Gate to Source Voltage

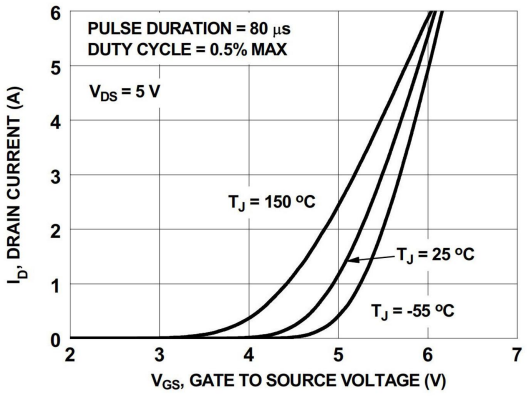


Figure 5. Transfer Characteristics

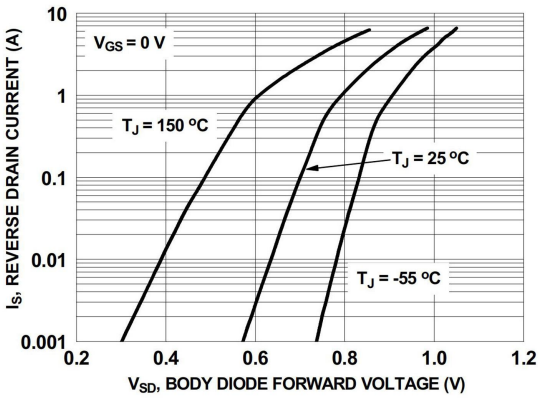


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

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Typical Characteristics T_J = 25 °C unless otherwise noted

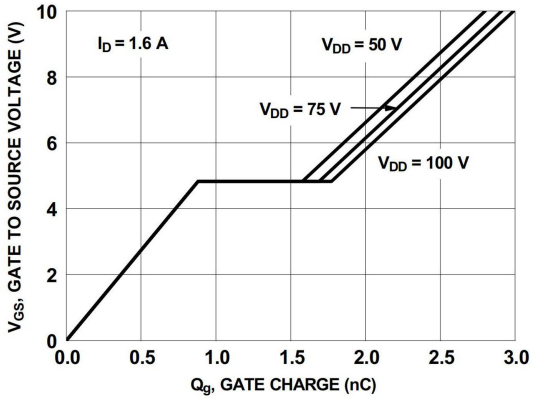


Figure 7. Gate Charge Characteristics

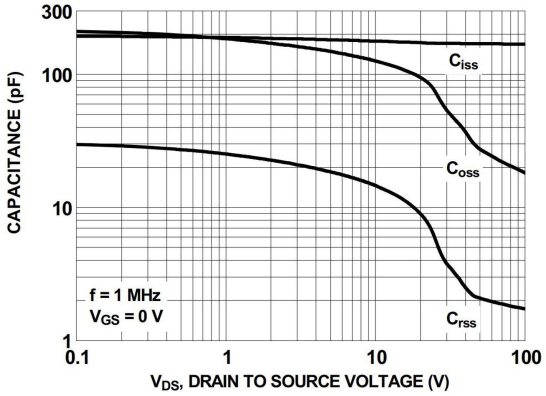


Figure 8. Capacitance vs Drain to Source Voltage

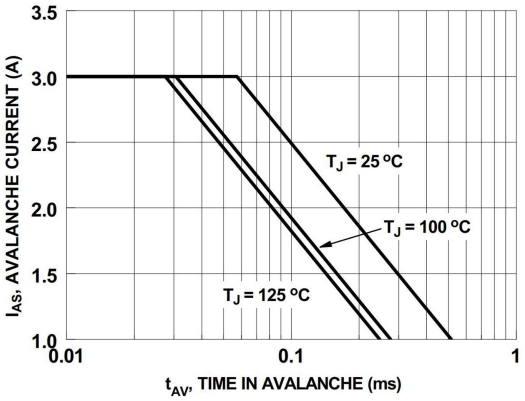


Figure 9. Unclamped Inductive Switching Capability

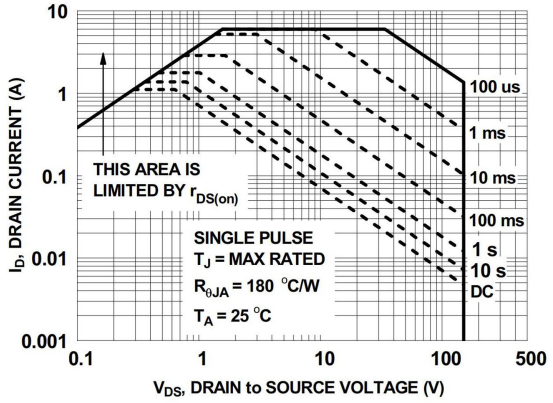


Figure 10. Forward Bias Safe Operating Area

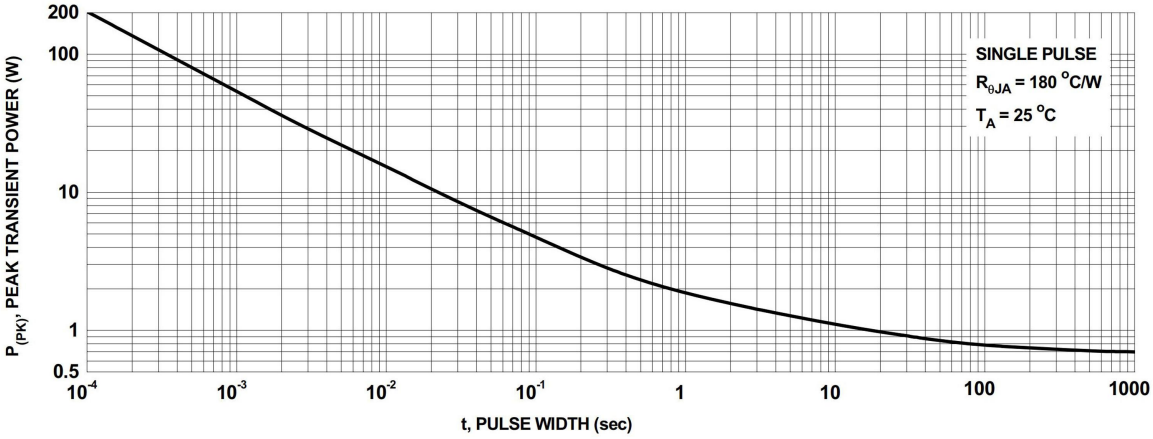


Figure 11. Single Pulse Maximum Power Dissipation

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Typical Characteristics T_J = 25 °C unless otherwise noted

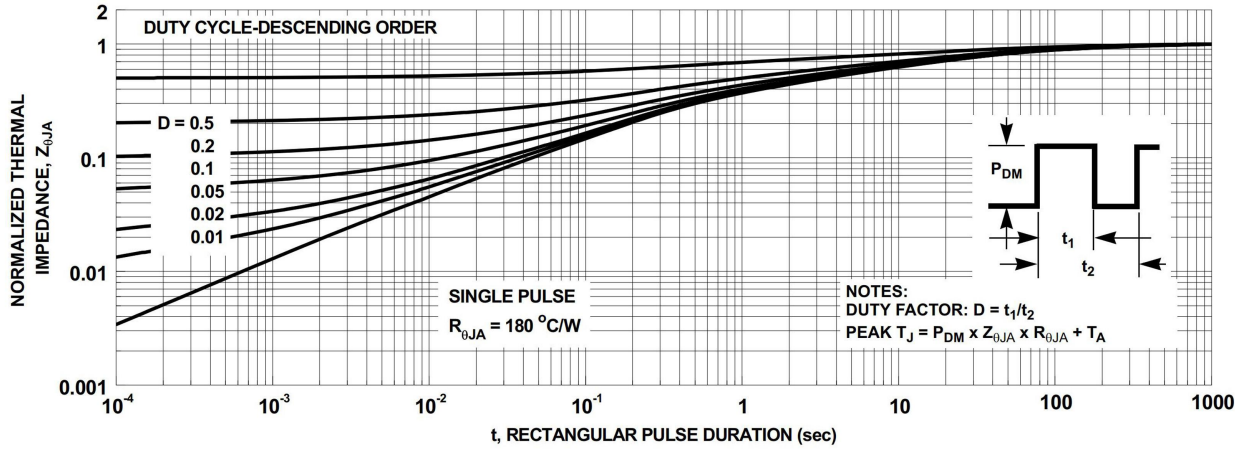


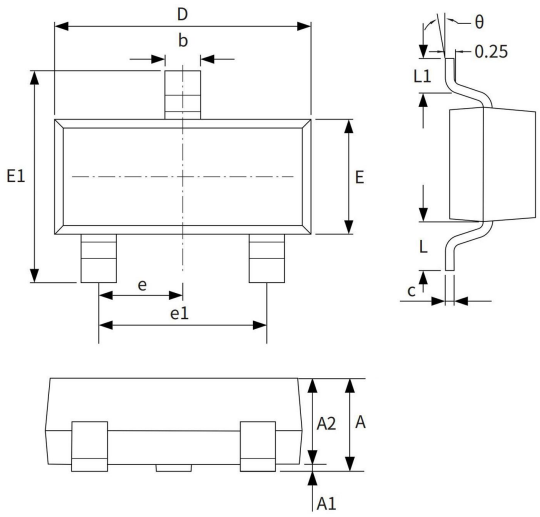
Figure 12. Junction-to-Ambient Transient Thermal Response Curve

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Ordering Information

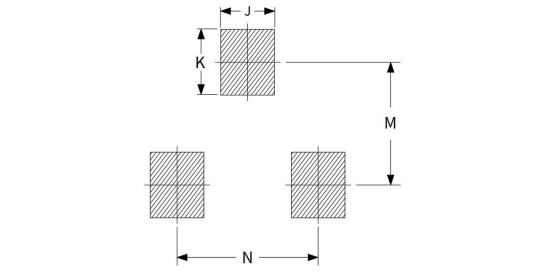
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077